Title (en)

SEMICONDUCTOR PACKAGE, SEMICONDUCTOR DEVICE, ELECTRONIC DEVICE, AND METHOD OF MANUFACTURING SEMICONDUCTOR PACKAGE

Title (de)

HALBLEITERGEHÄUSE, HALBLEITER, ELEKTRONIKELEMENT UND HERSTELLUNG EINES HALBLEITERGEHÄUSES

Title (fr)

BOITIER A SEMI-CONDUCTEUR, DISPOSITIF SEMI-CONDUCTEUR, DISPOSITIF ELECTRONIQUE ET PROCEDE DE FABRICATION DE BOITIER A SEMI-CONDUCTEUR

Publication

EP 1107307 A8 20011121 (EN)

Application

EP 00935668 A 20000613

Priority

- JP 0003836 W 20000613
- JP 16900899 A 19990615

Abstract (en)

[origin: EP1107307A1] An insulating layer (3) having an opening portion (3a) at a position conformable to an electrode pad (2) is formed. Next, a resin projection portion (4) is formed on the insulating layer (3). Thereafter, a resist film is formed which has opening portions made in regions conformable to the opening portion (3a), the resin projection portion (4) and the region sandwiched therebetween. A Cu plating layer (6) is formed by electrolytic copper plating, using the resist film as a mask. <IMAGE>

IPC 1-7

H01L 21/60; H01L 23/12

IPC 8 full level

H01L 21/56 (2006.01); **H01L 23/31** (2006.01); **H01L 23/485** (2006.01); **H01L 23/525** (2006.01)

CPC (source: EP US)

H01L 21/56 (2013.01 - EP US); **H01L 23/3107** (2013.01 - EP US); **H01L 23/3114** (2013.01 - EP US); **H01L 23/525** (2013.01 - EP US); **H01L 24/02** (2013.01 - EP); **H01L 24/03** (2013.01 - EP); **H01L 24/05** (2013.01 - EP); **H01L 24/10** (2013.01 - EP US); **H01L 24/13** (2013.01 - EP US); H01L 2224/02125 (2013.01 - EP US); H01L 2224/0231 (2013.01 - EP US); H01L 2224/02351 (2013.01 - EP US); H01L 2224/0236 (2013.01 - EP); H01L 2224/02377 (2013.01 - EP); H01L 2224/0401 (2013.01 - EP US); H01L 2224/05124 (2013.01 - EP US); H01L 2224/05147 (2013.01 - EP US); H01L 2224/05155 (2013.01 - EP US); H01L 2224/05166 (2013.01 - EP US); H01L 2224/05171 (2013.01 - EP US); H01L 2224/05548 (2013.01 - EP US); H01L 2224/05567 (2013.01 - EP US); H01L 2224/05572 (2013.01 - EP US); H01L 2224/05644 (2013.01 - EP US); H01L 2224/13 (2013.01 - EP US); H01L 2224/13021 (2013.01 - EP US); H01L 2224/13022 (2013.01 - EP US); H01L 2224/13023 (2013.01 - EP US); H01L 2224/13024 (2013.01 - EP); H01L 2224/13099 (2013.01 - EP US); H01L 2924/0001 (2013.01 - EP); H01L 2924/0002 (2013.01 - EP US); H01L 2924/01004 (2013.01 - EP US); H01L 2924/01005 (2013.01 - EP US); H01L 2924/01006 (2013.01 - EP US); H01L 2924/01013 (2013.01 - EP US); H01L 2924/01015 (2013.01 - EP US); H01L 2924/01022 (2013.01 - EP US); H01L 2924/01024 (2013.01 - EP US); H01L 2924/01029 (2013.01 - EP US); H01L 2924/01033 (2013.01 - EP US); H01L 2924/01078 (2013.01 - EP US); H01L 2924/01079 (2013.01 - EP US); H01L 2924/014 (2013.01 - EP US); H01L 2924/10329 (2013.01 - EP US); H01L 2924/14 (2013.01 - EP US); H01L 2924/15311 (2013.01 - EP US)

Citation (search report)

See references of WO 0077844A1

Cited by

EP1589329A4

Designated contracting state (EPC)

AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT

DOCDB simple family (publication)

EP 1107307 A1 20010613; **EP 1107307 A4 20011227**; **EP 1107307 A8 20011121**; **EP 1107307 B1 20050907**; AU 5109900 A 20010102; CA 2340677 A1 20001221; CA 2340677 C 20050705; DE 60022458 D1 20051013; DE 60022458 T2 20060622; JP 3651597 B2 20050525; US 2003207494 A1 20031106; US 2005037539 A1 20050217; US 6835595 B1 20041228; US 7023088 B2 20060404; US 7157363 B2 20070102; WO 0077844 A1 20001221

DOCDB simple family (application)

EP 00935668 A 20000613; AU 5109900 A 20000613; CA 2340677 A 20000613; DE 60022458 T 20000613; JP 0003836 W 20000613; JP 2001503223 A 20000613; US 44229803 A 20030521; US 74497601 A 20010604; US 94938604 A 20040927